

ABSTRACT OF THE DISCLOSURE

There is disclosed a method of fabricating a thin-film transistor having excellent characteristics. Nickel element is held in contact with selected regions of an amorphous silicon film. Then, thermal processing is performed to crystallize the amorphous film. Subsequently, thermal processing is carried out in an oxidizing ambient containing a halogen element to form a thermal oxide film. At this time, the crystallinity is improved. Also, gettering of the nickel element proceeds. This crystalline silicon film consists of crystals grown radially from a number of points. Consequently, the thin-film transistor having excellent characteristics can be obtained.